

Silicon PNP Power Transistors

2SB1470

DESCRIPTION

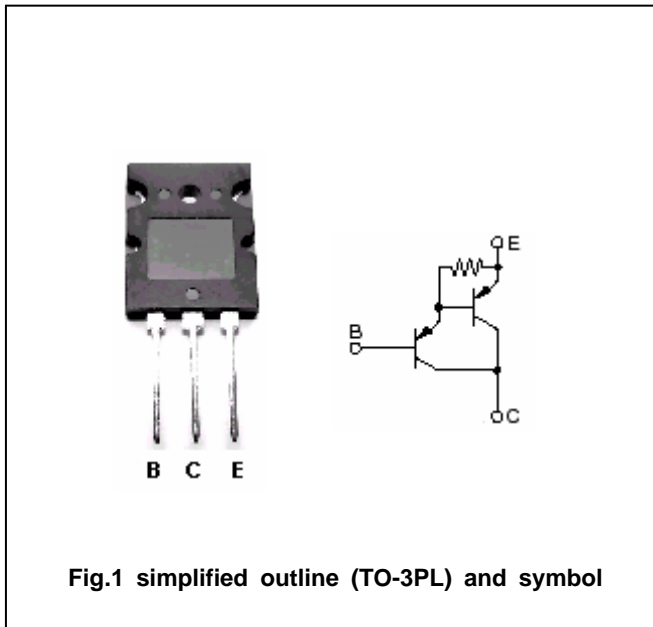
- With TO-3PL package
- Complement to type 2SD2222
- High DC current gain
- Low collector saturation voltage
- DARLINGTON

APPLICATIONS

- For power amplification

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-160	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-160	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-8	A
I <sub>CM</sub>	Collector current-peak		-15	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	120	W
		T <sub>a</sub> =25°C	3.5	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-30mA ; I <sub>B</sub> =0	-160			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-7A ; I <sub>B</sub> =-7mA			-3.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-7A ; I <sub>B</sub> =-7mA			-3.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-160V ; I <sub>E</sub> =0			-100	μ A
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =-160V ; I <sub>B</sub> =0			-100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-100	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	1000			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-7A ; V <sub>CE</sub> =-5V	3500		20000	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-10V ; f=1MHz		20		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =-7A ; I <sub>B1</sub> =-I <sub>B2</sub> =-7mA V <sub>CC</sub> =-50V		1.0		μ s
t <sub>s</sub>	Storage time			1.5		μ s
t <sub>f</sub>	Fall time			1.2		μ s

◆ h<sub>FE-2</sub> classifications

Q	S
3500-10000	7000-20000

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PACKAGE OUTLINE

